

2SC2914

SILICON NPN TRIPLE DIFFUSED TYPE

SWITCHING REGULATOR AND HIGH VOLTAGE
SWITCHING APPLICATIONS,
HIGH SPEED DC-DC CONVERTER APPLICATIONS.

FEATURES:

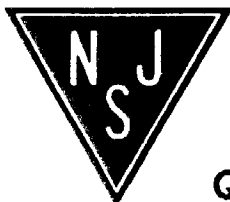
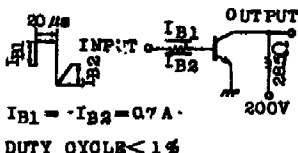
- . Excellent Switching Times
: $t_r=1.0\mu s$ (Max.), $t_f=1.0\mu s$ (Max.) at $I_C=7A$
- . High Collector Breakdown Voltage : $V_{CE0}=400V$

MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CB0}	500	V
Collector-Emitter Voltage	V_{CE0}	400	V
Emitter-Base Voltage	V_{EB0}	7	V
Collector Current	I_C	10	A
Base Current	I_B	3	A
Collector Power Dissipation (Tc=25°C)	P_C	120	W
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-65 ~ 150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB}=400V, I_E=0$	-	-	100	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=7V, I_C=0$	-	-	1	mA
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=1mA, I_E=0$	500	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=10mA, I_B=0$	400	-	-	V
DC Current Gain	h_{FE}	$V_{CE}=5V, I_C=5A$	12	-	-	
		$V_{CE}=5V, I_C=10A$	8	-	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=10A, I_B=2A$	-	-	1.0	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=10A, I_B=2A$	-	-	2.0	V
Switching Time	Rise Time	t_r	-	-	1.0	μs
	Storage Time	t_{stg}	-	-	2.5	
	Fall Time	t_f	-	-	1.0	



NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

Quality Semi-Conductors

Fig.2 outline dimensions (unindicated tolerance:±0.1mm)

